L Number	Hits	Search Text	DB	Time stamp
1	155	((ldd or (lightly near2 dop\$3)) same	USPAT;	2004/08/11 14:27
	133	(source and drain)) near10 simultan\$6	US-PGPUB;	2001/00/11 11:2/
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	65		USPAT;	2004/08/11 14:32
		(source and drain)) near5 simultan\$6	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
3	91	((ldd or (lightly near2 dop\$3)) same	USPAT;	2004/08/11 14:33
-		(source and drain)) near5 (simultan\$6 or	US-PGPUB;	
		"same" adj time)	EPO; JPO;	ļ
	:		DERWENT;	
		///3 44 6 /3 4 -3 -4 3 -4 3 -4 3 -4 3 -4 3 -4 3	IBM_TDB	2004/00/11 14:22
4	26		USPAT; US-PGPUB;	2004/08/11 14:33
}		<pre>(source and drain)) near5 (simultan\$6 or "same" adj time)) not (((ldd or (lightly</pre>	EPO; JPO;	
		near2 dop\$3)) same (source and drain))	DERWENT;	
		near5 simultan\$6)	IBM_TDB	
7	2	6452241.URPN.	USPĀT	2004/08/11 14:35
8	2	("5914498"   "6259120").PN.	USPAT	2004/08/11 14:36
-	10043	((438/149) or (438/151) or (438/163) or	USPAT;	2004/08/11 11:15
		(438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or	US-PGPUB; EPO; JPO;	
		(438/486) or (438/488) or (438/491) or	DERWENT;	
		(438/514) or (435/552) or (438/708) or	IBM TDB	
		(438/725) or (438/736) or (438/737)).CCLS.		
-	30291	ldd or (lightly near2 dop\$3)	USPAT;	2004/08/11 14:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	3632	(photo near2 resist) near2 (layer or film)	USPAT;	2004/08/11 11:04
	+ • <del>-</del>	same ((photo near2 mask\$1) or mask\$1)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	16061	(/noly near) erystall\$2\ er relat ===?	IBM_TDB	2004/08/11 11:09
-	16861	((poly near2 crystall\$3) or poly) near2 silicon	USPAT; US-PGPUB;	~UU4/UO/II II:U9
			EPO; JPO;	.
			DERWENT;	
			IBM_TDB	
-	458116	tft or (thin near2 film)	USPAT;	2004/08/11 11:15
			US-PGPUB; EPO; JPO;	
			DERWENT;	
[			IBM TDB	
-	337	(ldd or (lightly near2 dop\$3)) and ((photo	USPAT;	2004/08/10 19:39
		near2 resist) near2 (layer or film) same	US-PGPUB;	
		((photo near2 mask\$1) or mask\$1))	EPO; JPO;	
			DERWENT;	
_	10	(((ldd or (lightly near2 dop\$3)) and	USPAT;	2004/08/10 19:55
		((photo near2 resist) near2 (layer or	US-PGPUB;	
		film) same ((photo near2 mask\$1) or	EPO; JPO;	
]		<pre>mask\$1))) and (((poly near2 crystall\$3) or</pre>	DERWENT;	
		poly) near2 silicon)) and (tft or (thin	IBM_TDB	
_	1	near2 film)) (((438/149) or (438/151) or (438/163) or	USPAT;	2004/08/10 19:40
	<b>.</b>	(438/164) or $(438/166)$ or $(438/197)$ or	US-PGPUB;	2004/00/IU I3:40
		(438/301) or (438/365) or (438/369) or	EPO; JPO;	
		(438/486) or (438/488) or (438/491) or	DERWENT;	
		(438/514) or (435/552) or (438/708) or	IBM_TDB	
		(438/725) or (438/736) or	_	
]		(438/737)).CCLS.) and ((((ldd or (lightly		
		<pre>near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2</pre>		
		mask\$1) or mask\$1))) and ((poly near2		
		crystall\$3) or poly) near2 silicon)) and		
		(tft or (thin near2 film)))		

		1 ( ( 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	Lucham.	2004/00/10 10.55
-	5	(((ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or	USPAT; US-PGPUB;	2004/08/10 19:55
		film) same ((photo near2 mask\$1) or	EPO; JPO;	
		mask\$1))) and (((poly near2 crystall\$3) or	DERWENT;	
		poly) near2 silicon)) and (((438/149) or	IBM TDB	
		(438/151) or (438/163) or (438/164) or	_	
	}	(438/166) or (438/197) or (438/301) or		
		(438/365) or (438/369) or (438/486) or		
		(438/488) or (438/491) or (438/514) or		
		(435/552) or (438/708) or (438/725) or		
	20	(438/736) or (438/737)).CCLS.)	I HODAM.	2004/00/10 20:06
_	38		USPAT;	2004/08/10 20:06
		((photo near2 resist) near2 (layer or	US-PGPUB; EPO; JPO;	
		film) same ((photo near2 mask\$1) or mask\$1))) and (((poly near2 crystall\$3) or	DERWENT;	
		poly) near2 silicon)	IBM TDB	
_	2	1	USPAT;	2004/08/10 20:07
	_	film) same ((photo near2 mask\$1) or	US-PGPUB;	
		mask\$1)) same (((poly near2 crystall\$3) or		
		poly) near2 silicon)) and (ldd or (lightly	DERWENT;	
		near2 dop\$3))) and (((438/149) or	IBM_TDB	
		(438/151) or (438/163) or (438/164) or		
		(438/166) or (438/197) or (438/301) or		
		(438/365) or (438/369) or (438/486) or		
	1	(438/488) or (438/491) or (438/514) or		
	1	(435/552) or (438/708) or (438/725) or		
_	11	(438/736) or (438/737)).CCLS.) (((photo near2 resist) near2 (layer or	USPAT;	2004/08/10 20:08
-	1	film) same ((photo near2 mask\$1) or	US-PGPUB;	2004/00/10 20.00
		mask\$1)) same (((poly near2 crystall\$3) or	EPO; JPO;	
		poly) near2 silicon)) and (ldd or (lightly		
		near2 dop\$3))	IBM TDB	
_	64	((photo near2 resist) near2 (layer or	USPAT;	2004/08/10 20:16
		film) same ((photo near2 mask\$1) or	US-PGPUB;	
		mask\$1)) same (((poly near2 crystall\$3) or	EPO; JPO;	
		poly) near2 silicon)	DERWENT;	
			IBM_TDB	
-	10301	i '	USPAT;	2004/08/10 20:16
		(lightly near2 dop\$3))	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	į
_	803	((source same drain) near10 (ldd or	USPAT;	2004/08/10 20:17
		(lightly near2 dop\$3))) and (((poly near2	US-PGPUB;	
		crystall\$3) or poly) near2 silicon)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	372	(((source same drain) near10 (ldd or	USPAT;	2004/08/10 20:17
		(lightly near2 dop\$3))) and (((poly near2	US-PGPUB;	
		crystall\$3) or poly) near2 silicon)) and	EPO; JPO;	
		(tft or (thin near2 film))	DERWENT;	
		////0000000 0000 00000 000000 000000 000000	IBM_TDB	2004/00/10 20:17
-	36	<pre>((((source same drain) near10 (ldd or (lightly near2 dop\$3))) and (((poly near2</pre>	USPAT; US-PGPUB;	2004/08/10 20:17
		crystall\$3) or poly) near2 silicon)) and	EPO; JPO;	
		(tft or (thin near2 film))) and	DERWENT;	
		(((438/149) or (438/151) or (438/163) or	IBM TDB	
		(438/164) or (438/166) or (438/197) or	<b></b>	
		(438/301) or (438/365) or (438/369) or		
	Í	(438/486) or (438/488) or (438/491) or		
		(438/514) or (435/552) or (438/708) or	•	į į
		(438/725) or (438/736) or		
	_	(438/737)).CCLS.)		
] -	3093	1 12	USPAT;	2004/08/10 21:07
		same ((photo near2 mask\$1) or mask\$1)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	<u> </u>		IBM_TDB	<u></u>

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			·	
-	159		USPAT;	2004/08/10 20:29
		same ((photo near2 mask\$1) or mask\$1)) and	US-PGPUB;	
		((source same drain) near10 (ldd or	EPO; JPO;	
		(lightly near2 dop\$3)))	DERWENT; IBM TDB	
	13	(((photo near2 resist) near5 (pattern\$3)	USPAT;	2004/08/10 20:26
_	13	same ((photo near2 mask\$1) or mask\$1)) and	US-PGPUB;	2004/00/10 20:20
		((source same drain) near10 (ldd or	EPO; JPO;	
		(lightly near2 dop\$3)))) and (((438/149)	DERWENT;	
		or (438/151) or (438/163) or (438/164) or	IBM TDB	
		(438/166) or (438/197) or (438/301) or	1511_155	
		(438/365) or (438/369) or (438/486) or		
		(438/488) or (438/491) or (438/514) or		
		(435/552) or (438/708) or (438/725) or		
		(438/736) or (438/737)).CCLS.)		
_	0		USPAT;	2004/08/10 20:29
	_	same ((photo near2 mask\$1) or mask\$1)) and	US-PGPUB;	
		((source same drain) near10 (ldd or	EPO; JPO;	
		(lightly near2 dop\$3)))) and (((438/149)	DERWENT;	
		or (438/151) or (438/163) or (438/164) or	IBM TDB	
		(438/166) or (438/197) or (438/301) or	<u> </u>	
		(438/365) or (438/369) or (438/486) or		
		(438/488) or (438/491) or (438/514) or		
	•	(435/552) or (438/708) or (438/725) or		
		(438/736) or (438/737)).CCLS.)) not		
		(((photo near2 resist) near5 (pattern\$3)		
		same ((photo near2 mask\$1) or mask\$1)) and		
		((source same drain) near10 (ldd or		1
		(lightly near2 dop\$3))))		
-	146	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2004/08/10 20:29
		same ((photo near2 mask\$1) or mask\$1)) and	US-PGPUB;	
		((source same drain) near10 (ldd or	EPO; JPO;	
		(lightly near2 dop\$3)))) not (((photo	DERWENT;	
		near2 resist) near5 (pattern\$3) same	IBM_TDB	
		((photo near2 mask\$1) or mask\$1)) and		
	ł	((source same drain) near10 (ldd or		
		(lightly near2 dop\$3)))) and (((438/149)		
		or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or		
		(438/365) or (438/369) or (438/486) or		
		(438/488) or (438/491) or (438/514) or		
		(435/552) or (438/708) or (438/725) or		
		(438/736) or (438/737)).CCLS.))		
_	31623		USPAT;	2004/08/10 21:14
		(pattern\$3) same ((photo near2 mask\$1) or	US-PGPUB;	
		mask\$1)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	104	(((photo near2 resist) or resist) near5	USPAT;	2004/08/10 20:42
		(pattern\$3) same ((photo near2 mask\$1) or	US-PGPUB;	
		mask\$1)) same ((source same drain) near10	EPO; JPO;	
	1	(ldd or (lightly near2 dop\$3)))	DERWENT;	
			IBM_TDB	
_	10	, , , , <u>, , , , , , , , , , , , , , , </u>	USPAT;	2004/08/10 20:44
		(pattern\$3) same ((photo near2 mask\$1) or	US-PGPUB;	
		mask\$1)) same ((source same drain) near10	EPO; JPO;	
		(ldd or (lightly near2 dop\$3)))) and	DERWENT;	
		(((poly near2 crystall\$3) or poly) near2	IBM_TDB	]
	120	silicon)	11000	2004/00/10 00 ::
<b>-</b>	136		USPAT;	2004/08/10 20:44
		(pattern\$3) same ((photo near2 mask\$1) or	US-PGPUB;	
}		mask\$1)) same (((poly near2 crystall\$3) or	EPO; JPO;	
		poly) near2 silicon)	DERWENT; IBM TDB	
_	31	((((photo near2 resist) or resist) near5	USPAT;	2004/08/10 20:44
		(pattern\$3) same ((photo near2 mask\$1) or	US-PGPUB;	2004/00/10 20:44
		mask\$1)) same ((poly near2 crystall\$3) or	EPO; JPO;	
		poly) near2 silicon) ) and (ldd or	DERWENT;	
		(lightly near2 dop\$3))	IBM TDB	
<u> </u>	I			I

			· · · · · · · · · · · · · · · · · · ·	
_	30	<pre>((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 20:51
_	117	((photo near2 resist) or resist) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 20:55
	36	(((photo near2 resist) or resist) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:52
	31	(435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.) ((((photo near2 resist) or resist) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)) not (((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:52
-	307	(ldd or (lightly near2 dop\$3))) ((photo near2 resist) or resist) near10 (((poly near2 crystall\$3) or poly) near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 20:56
_	198	((photo near2 resist) or resist) near5 (((poly near2 crystall\$3) or poly) near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 20:58
	9	(((photo near2 resist) or resist) near5 (((poly near2 crystall\$3) or poly) near2 silicon)) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 20:56
_	229	<pre>(photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((ion near2 implant\$4) or dop\$)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/10 21:22
	6	(((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((ion near2 implant\$4) or dop\$) ) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 21:09

73 ((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) us-PGPUB; near10 ((ion near2 implant\$4) or dop\$) ) and (ldd or (lightly near2 dop\$3))  - 56 ((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon  - 7 ((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) or poly) near2 silicon is near5 (layer or film) same ((photo near2 mask\$1) or mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon is near5 (layer or film) same ((438/149) or (438/151) or (438/163) or (438/164) or (438/151) or (438/165) or (438/365) or (438/369) or (438/486) or	10 21:17
near10 ((ion near2 implant\$4) or dop\$) ) and (ldd or (lightly near2 dop\$3))  56 ((photo near2 resist) or resist) near5	
and (ldd or (lightly near2 dop\$3))  ((photo near2 resist) or resist) near5 ((pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon  (((photo near2 resist) or resist) near5 ((ayer or film) same ((photo near2 mask\$1)) or mask\$1) near10 ((poly near2 crystall\$3) or (USPAT; (layer or film) same ((photo near2 mask\$1)) or mask\$1) near10 ((poly near2 crystall\$3) or (JPO; or poly) near2 silicon) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or	
TDB	
- ((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon  7 (((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) USPĀT; (layer or film) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or	
(pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon  ((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon) and ((438/149) or (438/151) or (438/163) or (438/164) or (438/365) or (438/369) or (438/486) or  (photo near2 resist) or resist) near5 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon  7 (((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/365) or (438/369) or (438/486) or  [	10 21:18
poly) near2 silicon  7 (((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) us-PGPUB; or mask\$1) near10 ((poly near2 crystall\$3) EPO; JPO; or poly) near2 silicon) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or	10 21:18
7 (((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or	10 21:18
(layer or film) same ((photo near2 mask\$1) US-PGPUB; or mask\$1) near10 ((poly near2 crystall\$3) EPO; JPO; or poly) near2 silicon) and (((438/149) or DERWENT; (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or	10 21:18
or mask\$1) near10 ((poly near2 crystall\$3) EPO; JPO; or poly) near2 silicon) and (((438/149) or DERWENT; (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or	
or poly) near2 silicon) and (((438/149) or DERWENT; (438/151) or (438/163) or (438/164) or IBM_TDB (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or	
(438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or	
(438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or	
(438/365) or (438/369) or (438/486) or	
(438/488) or (438/491) or (438/514) or	
(435/552) or (438/708) or (438/725) or	
(438/736) or (438/737)).CCLS.)	
- 94 ((photo near2 resist) or resist) near5 USPAT; 2004/08/	10 21:19
(layer or film) same ((photo near2 mask\$1) US-PGPUB;	
or mask\$1) near10 ((poly near2 crystall\$3)   EPO; JPO;	
or poly) near2 silicon DERWENT;	
IBM_TDB	10 0
- 157 (photo near2 resist) near5 (pattern\$3) USPAT; 2004/08/	10 21:31
same ((photo near2 mask\$1) or mask\$1) US-PGPUB;	
near5 ((ion near2 implant\$4) or dop\$) EPO; JPO;	
DERWENT; IBM TDB	
- 10 ((photo near2 resist) near5 (pattern\$3) USPAT; 2004/08/	10 21.25
same ((photo near2 mask\$1) or mask\$1) US-PGPUB;	21.20
near5 ((ion near2 implant\$4) or dop\$) ) EPO; JPO;	
and (((poly near2 crystall\$3) or poly) DERWENT;	
near2 silicon) IBM_TDB	
- 48 ((photo near2 resist) near5 (pattern\$3) USPAT; 2004/08/	10 21:25
same ((photo near2 mask\$1) or mask\$1) US-PGPUB;	
near5 ((ion near2 implant\$4) or dop\$) ) EPO; JPO;	
and (tft or (thin near2 film))  DERWENT;	
IBM_TDB	10 21.32
same ((photo near2 mask\$1) or mask\$1) US-PGPUB;	10 21.52
near5 ((ion near2 implant\$4) or dop\$) same EPO; JPO;	
((poly near2 crystall\$3) or poly) near2 DERWENT;	
silicon   IBM_TDB	
- 20174 (((photo near2 resist) or ((photo or USPAT; 2004/08/	11 11:56
light) near2 sensitive) or resist) near2 US-PGPUB;	
(layer or film)) near10 ((photo near2 EPO; JPO;	
mask\$1) or mask\$1) DERWENT;	
- 16861 ((poly near2 crystall\$3) or poly) near2 USPAT; 2004/08/	11 11.10
silicon   SPAT;   2004/08/	11:10
EPO; JPO;	
DERWENT;	
IBM TDB	
- 303223 (ion near2 implant\$4) or dop\$3 USPAT; 2004/08/	11 11:16
US-PGPUB;	
EPO; JPO;	
DERWENT;	
IBM_TDB	19 44
- 124 ((((photo near2 resist) or ((photo or USPAT; 2004/08/	11:14
light) near2 sensitive) or resist) near2 US-PGPUB;	
(layer or film)) near10 ((photo near2 EPO; JPO; mask\$1) or mask\$1)) same (((poly near2 DERWENT;	
crystall\$3) or poly) near2 silicon) IBM TDB	
- 84 (((((photo near2 resist) or ((photo or USPAT; 2004/08/	11 11.18
light) near2 sensitive) or resist) near2 US-PGPUB;	
(layer or film)) near10 ((photo near2 EPO; JPO;	
mask\$1) or mask\$1)) same (((poly near2 DERWENT;	
crystall\$3) or poly) near2 silicon)) and IBM_TDB	
((ion near2 implant\$4) or dop\$3)	

-	511		USPAT;	2004/08/11 11:14
		light) near2 sensitive) or resist) near2	US-PGPUB;	
		(layer or film)) near10 ((photo near2	EPO; JPO; DERWENT;	
		mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)	IBM TDB	
_	391	l	USPAT;	2004/08/11 11:14
	391	light) near2 sensitive) or resist) near2	US-PGPUB;	2004/00/11 11:14
		(layer or film)) near10 ((photo near2	EPO; JPO;	
		mask\$1) or mask\$1)) and (((poly near2	DERWENT;	
		crystall\$3) or poly) near2 silicon)) and	IBM TDB	
		((ion near2 implant\$4) or dop\$3)	<u> </u>	
_	458116	tft or (thin near2 film)	USPAT;	2004/08/11 11:15
			US-PGPUB;	
			EPO; JPO;	,
			DERWENT;	
	1.01	//////phaka maano maaisho an //mhaka an	IBM_TDB	2004/00/11 11:47
_	191	· · · · · · · · · · · · · · · · · · ·	USPAT; US-PGPUB;	2004/08/11 11:47
		light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2	EPO; JPO;	
		mask\$1) or mask\$1)) and ((poly near2	DERWENT;	
		crystall\$3) or poly) near2 silicon)) and	IBM TDB	
		((ion near2 implant\$4) or dop\$3)) and (tft	_	
		or (thin near2 film))		
-	10043	((438/149) or (438/151) or (438/163) or	USPAT;	2004/08/11 11:15
		(438/164) or (438/166) or (438/197) or	US-PGPUB;	
,		(438/301) or (438/365) or (438/369) or	EPO; JPO;	
}		(438/486) or (438/488) or (438/491) or	DERWENT;	
		(438/514) or (435/552) or (438/708) or	IBM_TDB	
	19	(438/725) or (438/736) or (438/737)).CCLS.	USPAT;	2004/08/11 11:16
	19	light) near2 sensitive) or resist) near2	US-PGPUB;	2004/00/11 11.10
		(layer or film)) near10 ((photo near2	EPO; JPO;	
		mask\$1) or mask\$1)) and ((poly near2	DERWENT;	
		crystall\$3) or poly) near2 silicon)) and	IBM TDB	
		((ion near2 implant\$4) or dop\$3)) and (tft	_	
		or (thin near2 film))) and (((438/149) or		
		(438/151) or (438/163) or (438/164) or		
		(438/166) or (438/197) or (438/301) or		
		(438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or		
		(435/552) or (438/708) or (438/725) or		
		(438/736) or (438/737)).CCLS.)		
_	172		USPAT;	2004/08/11 11:34
		light) near2 sensitive) or resist) near2	US-PGPUB;	, , , , , , , , , , , , , , , , , , , ,
		(layer or film)) near10 ((photo near2	EPO; JPO;	
		mask\$1) or mask\$1)) and (((poly near2	DERWENT;	
		crystall\$3) or poly) near2 silicon)) and	IBM_TDB	
		((ion near2 implant\$4) or dop\$3)) and (tft		
		or (thin near2 film))) not (((((((photo		
		near2 resist) or ((photo or light) near2		
		sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or	, i	
		mask\$1)) and (((poly near2 crystall\$3) or		
		poly) near2 silicon)) and ((ion near2		
]		implant\$4) or dop\$3)) and (tft or (thin		
		near2 film))) and (((438/149) or (438/151)		
		or (438/163) or (438/164) or (438/166) or		
]		(438/197) or (438/301) or (438/365) or		
		(438/369) or (438/486) or (438/488) or		
	!	(438/491) or (438/514) or (435/552) or		
		(438/708) or (438/725) or (438/736) or (438/737)).CCLS.))		
		/200/101//.COD0.//		<u>[</u>

0	((((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film)) not ((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/364) or (438/488) or (438/491) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))) not (((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:34
219		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 11:35

<u> </u>	200	((((((photo near2 resist) or ((photo or	USPAT;	2004/08/11 11:47
	200	light) near2 sensitive) or resist) near2	US-PGPUB;	2001,00, 22 2201
		(layer or film)) near10 ((photo near2	EPO; JPO;	
		mask\$1) or mask\$1)) and (((poly near2	DERWENT;	
		crystall\$3) or poly) near2 silicon)) and	IBM_TDB	
		((ion near2 implant\$4) or dop\$3)) not		
		((((((((photo near2 resist) or ((photo or		
		light) near2 sensitive) or resist) near2		
		(layer or film)) near10 ((photo near2		
		mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and		
		((ion near2 implant\$4) or dop\$3)) and (tft		
		or (thin near2 film))) not ((((((photo		
		near2 resist) or ((photo or light) near2		
		sensitive) or resist) near2 (layer or		
		film)) near10 ((photo near2 mask\$1) or		
		mask\$1)) and (((poly near2 crystall\$3) or		
		poly) near2 silicon)) and ((ion near2		
		implant\$4) or dop\$3)) and (tft or (thin		
		near2 film))) and (((438/149) or (438/151)		
		or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or		
		(438/369) or (438/486) or (438/488) or		
		(438/491) or (438/514) or (435/552) or		
		(438/708) or (438/725) or (438/736) or		
		(438/737)).CCLS.)))) not (((((photo near2		
		resist) or ((photo or light) near2		
		sensitive) or resist) near2 (layer or		
		film)) near10 ((photo near2 mask\$1) or		
		mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin		
	,	near2 film)))		
_	215	1 · · · ·	USPAT;	2004/08/11 11:49
		light) near2 sensitive) or resist) near2	US-PGPUB;	
		(layer or film)) near10 ((photo near2	EPO; JPO;	
		mask\$1) or mask\$1)) and (((poly near2	DERWENT;	
		crystall\$3) or poly) near2 silicon)) and	IBM_TDB	
_	16906	<pre>(tft or (thin near2 film)) (((photo near2 resist) or ((photo or</pre>	USPAT;	2004/08/11 11:57
_	10300	light) near2 sensitive) or resist) near2	US-PGPUB;	2004/00/11 11.5/
		(layer or film)) near5 ((photo near2	EPO; JPO;	
		mask\$1) or mask\$1)	DERWENT;	
			IBM_TDB	
-	1373	((((photo near2 resist) or ((photo or	USPAT;	2004/08/11 11:58
		light) near2 sensitive) or resist) near2	US-PGPUB;	
		(layer or film)) near5 ((photo near2	EPO; JPO;	
		<pre>mask\$1) or mask\$1)) same (tft or (thin near2 film))</pre>	DERWENT; IBM TDB	
_	507	1	USPAT;	2004/08/11 11:59
		light) near2 sensitive) or resist) near2	US-PGPUB;	
		(layer or film)) near5 ((photo near2	EPO; JPO;	
		mask\$1) or mask\$1)) same (tft or (thin	DERWENT;	
		near2 film))) and ((ion near2 implant\$4)	IBM_TDB	
	_	or dop\$3)	IIODAM.	0004/00/11 10 00
_	5	("5037766"   "5372958"   "5462887"     "5504019"   "5529937").PN.	USPAT	2004/08/11 12:29
_	2	("5985741"   "6066547").PN.	USPAT	2004/08/11 12:39
_	18		USPAT	2004/08/11 12:33
		"4764483"   "4824802"   "4865952"		,,
		"4902899"   "4952274"   "5077234"		
		"5110410"   "5139608"   "5175122"		
		"5286581"   "5296092"   "5310621"		
	5	"5350486"   "5362591"   "5418093").PN.	lieby.m	2004/00/11 12:44
_	5	("5412493"   "5736751"   "5962916"     "6365936"   "6384427").PN.	USPAT	2004/08/11 12:44
-	1	6624443.URPN.	USPAT	2004/08/11 12:45
-	3	("4231811"   "5985766"   "6043000").PN.	USPAT	2004/08/11 12:46
_	0	6410211.URPN.	USPAT	2004/08/11 12:46
_	9	("3920483"   "3997367"   "4035226"	USPAT	2004/08/11 12:47
	1	"4137458"   "4140913"   "4144101"		
	<u></u>	"4149904"   "4163155"   "4182023").PN.		